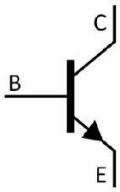
TO-92 NPN Silicon NPN transistor in a TO-92 Plastic Package.

High f_T

1.0mA 30mA

Use as RF amplifiers, oscillators and multipliers with collector currents in the1.0mA 30mA range.



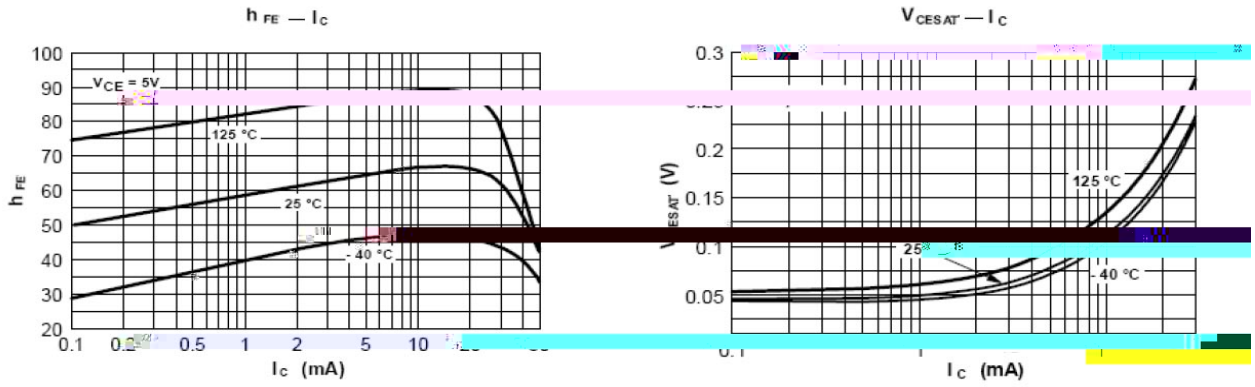


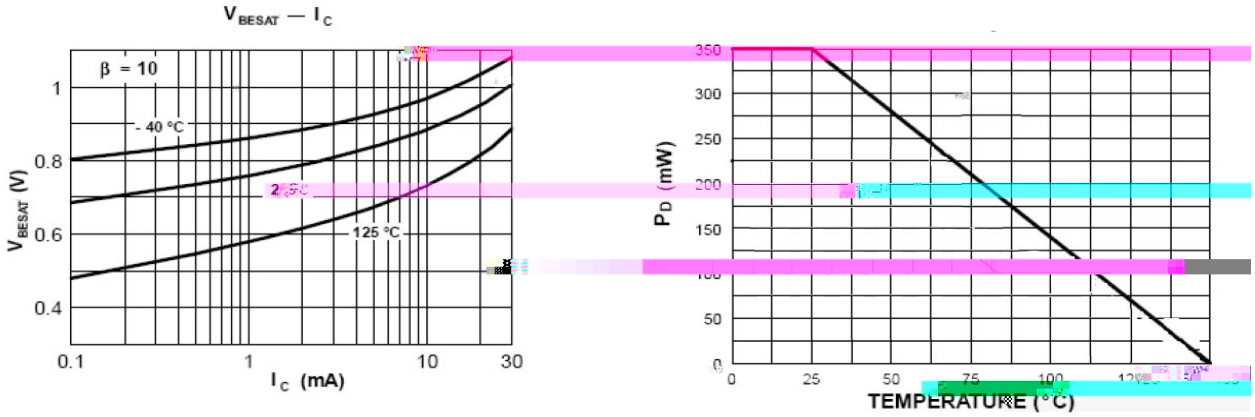
PIN1 Collector PIN 2 Base PIN 3 Emitter

See Marking Instructions.

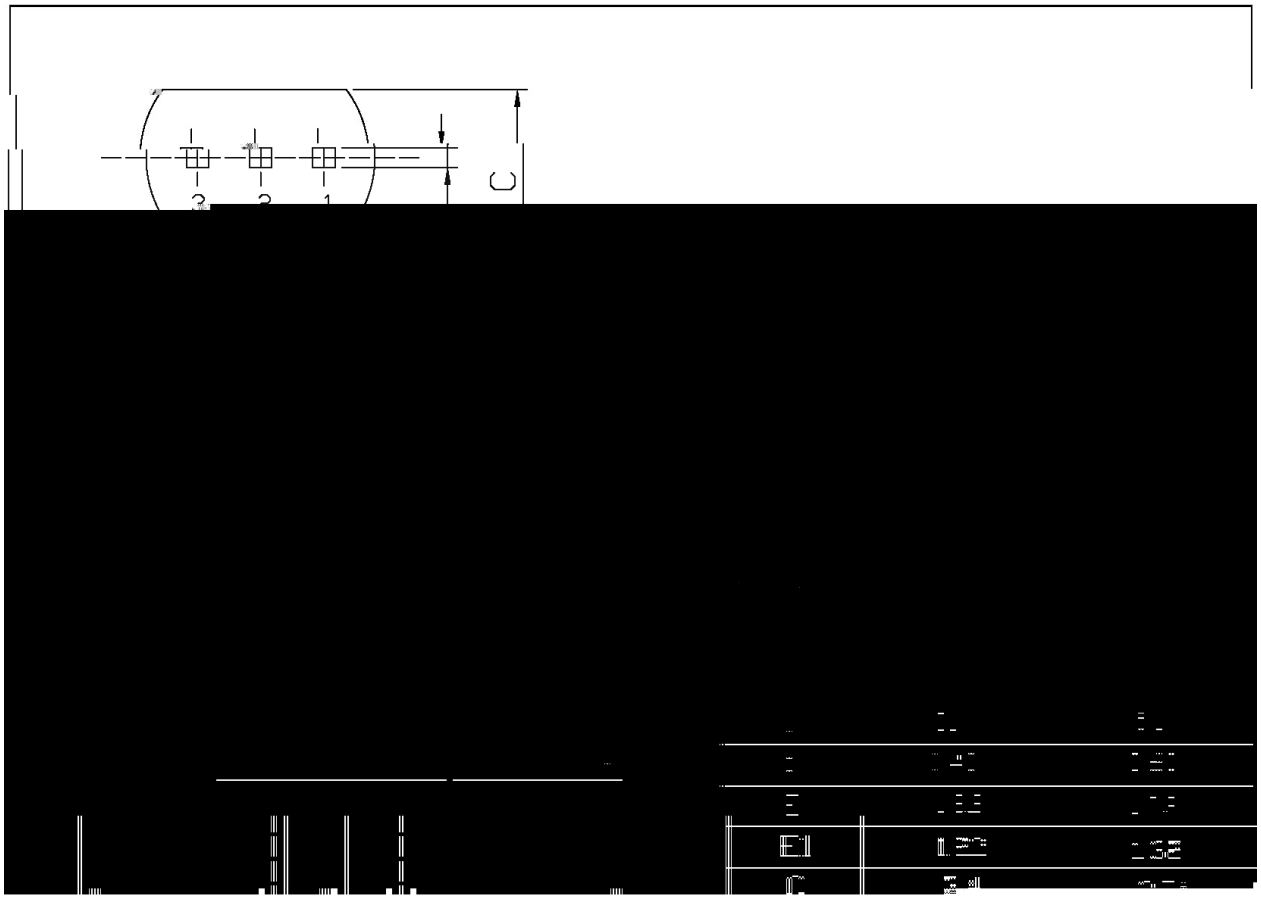
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	15	V
Emitter to Base Voltage	V_{EBO}	4.5	V
Collector Current - Continuous	I_C	50	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

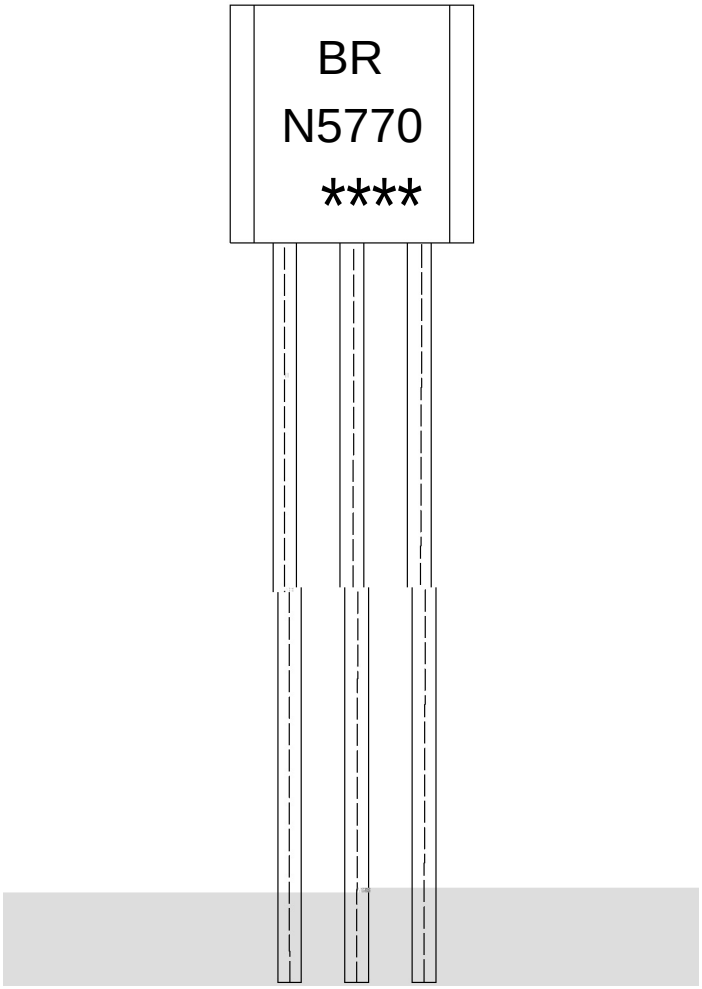
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=1.0μA I_E=0	30			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=3.0mA I_B=0	15			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=10μA I_C=0	4.5			V


h FE — I C
100
90
80
70
60
50
40
30
20
VCE = 5V
125 °C
25 °C
- 40 °C
h FE
0.1
0.5
1
2
5
10
I C (mA)
V CESAT — I C
0.3
0.2
0.15
0.1
0.05
V CESAT (V)
125 °C
25
- 40 °C
I C (mA)


V BESAT — I C
β = 10
1
0.8
0.6
0.4
V BESAT (V)
- 40 °C
25 °C
125 °C
0.1
1
10
30
I C (mA)
350
300
250
200
150
50
0
P D (mW)
0
25
50
75
TEMPERATURE (°C)

TO-92 Unit: mm





BR

N5770

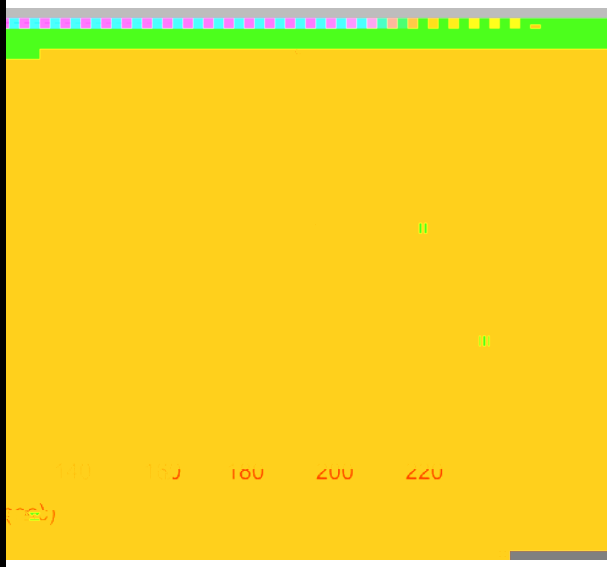
****

Note:

BR: Company Code.

N5770: Product Type.

****: Lot No. Code, code change with Lot No.



Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

Temp.:270±5 Time:10±1 sec

		Dimension		(unit mm3)
Box	Units/Outer Box	Bag	Inner Box	Outer Box
	/			